

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSIII)

2SK2717

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

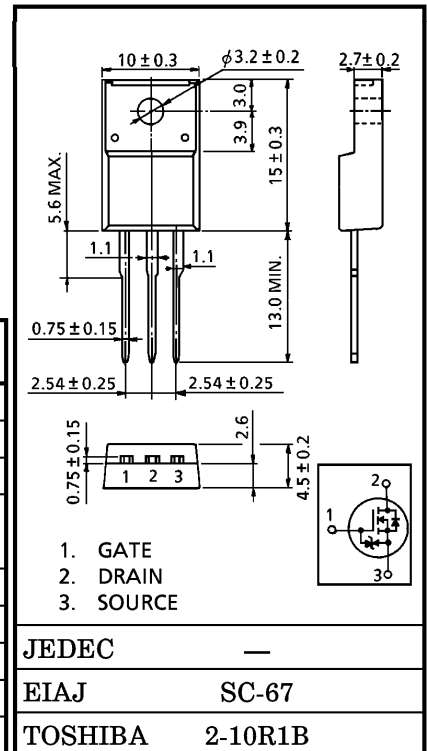
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 2.3\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.4S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 720V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	900	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	900	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	I_D	5	A
	I_{DP}	15	
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	45	W
Single Pulse Avalanche Energy**	E_{AS}	595	mJ
Avalanche Current	I_{AR}	5	A
Repetitive Avalanche Energy*	E_{AR}	4.5	mJ
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$



Weight : 1.9g (Typ.)

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.78	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90V, T_{ch} = 25^\circ C$ (initial), $L = 43.6mH, R_G = 25\Omega, I_{AR} = 5A$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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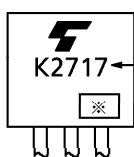
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	—	—	±10	μA
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = ±10μA, V _{DS} = 0V	±30	—	—	V
Drain Cut-off Current	I _{DSS}	V _{DS} = 720V, V _{GS} = 0V	—	—	100	μA
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 10mA, V _{GS} = 0V	900	—	—	V
Gate Threshold Voltage	V _{th}	V _{DS} = 10V, I _D = 1mA	2.0	—	4.0	V
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 3.0A	—	2.3	2.5	Ω
Forward Transfer Admittance	Y _{fs}	V _{DS} = 20V, I _D = 3.0A	1.1	4.4	—	S
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V f = 1MHz	—	1200	—	pF
Reverse Transfer Capacitance	C _{rss}		—	20	—	
Output Capacitance	C _{oss}		—	120	—	
Switching Time	Rise Time	t _r		—	40	ns
	Turn-on Time	t _{on}		—	90	
	Fall Time	t _f		—	60	
	Turn-off Time	t _{off}		V _{IN} : t _r , t _f < 5ns Duty ≤ 1%, t _w = 10μs	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q _g	V _{DD} ≈ 400V, V _{GS} = 10V, I _D = 5A	—	45	—	nC
Gate-Source Charge	Q _{gs}		—	25	—	
Gate-Drain ("Miller") Charge	Q _{gd}		—	20	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I _{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I _{DRP}	—	—	—	15	A
Diode Forward Voltage	V _{DSF}	I _{DR} = 5A, V _{GS} = 0V	—	—	-1.9	V
Reverse Recovery Time	t _{rr}	I _{DR} = 5A, V _{GS} = 0V	—	1300	—	ns
Reverse Recovery Charge	Q _{rr}		dI _{DR} / dt = 100A / μs	—	11	—

MARKING



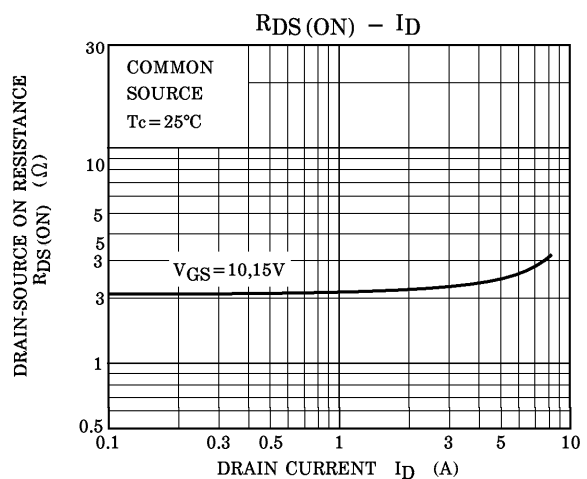
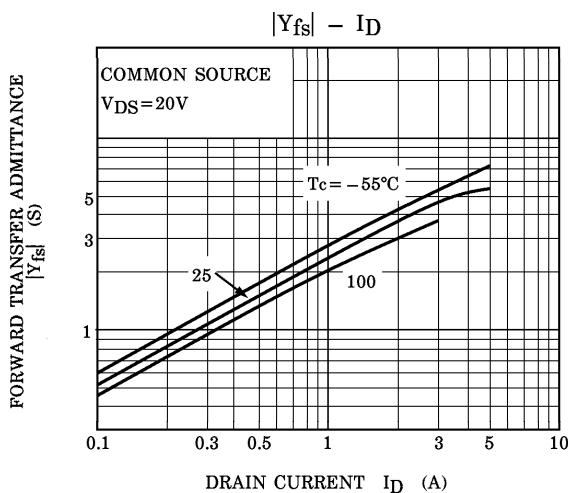
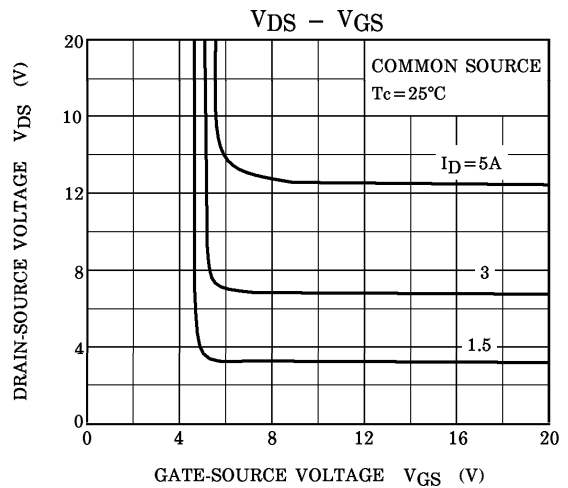
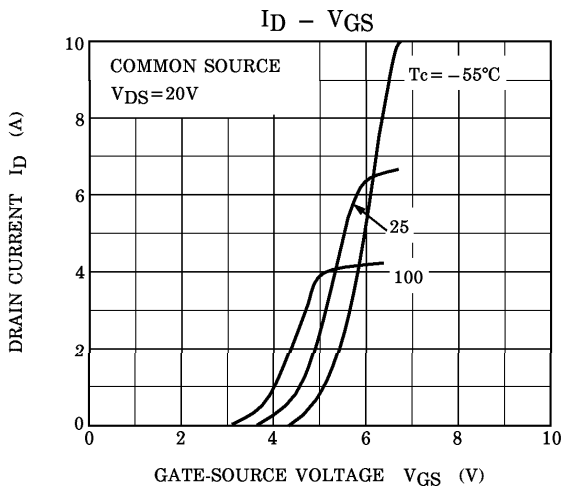
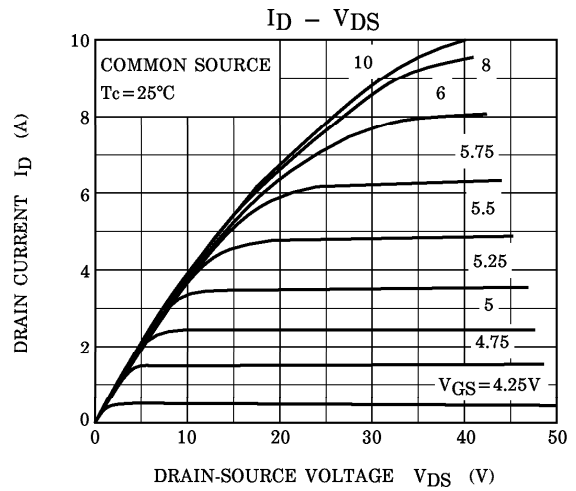
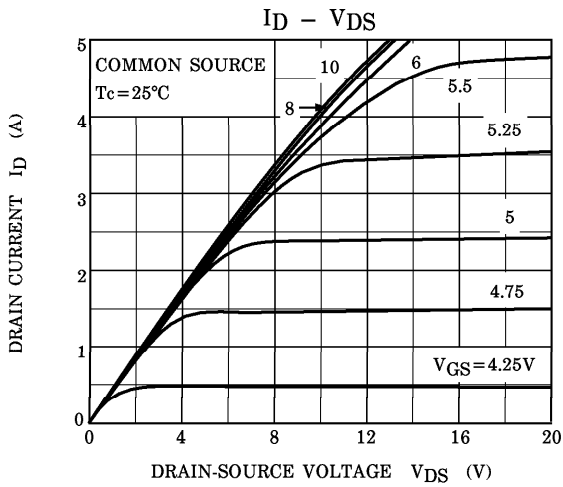
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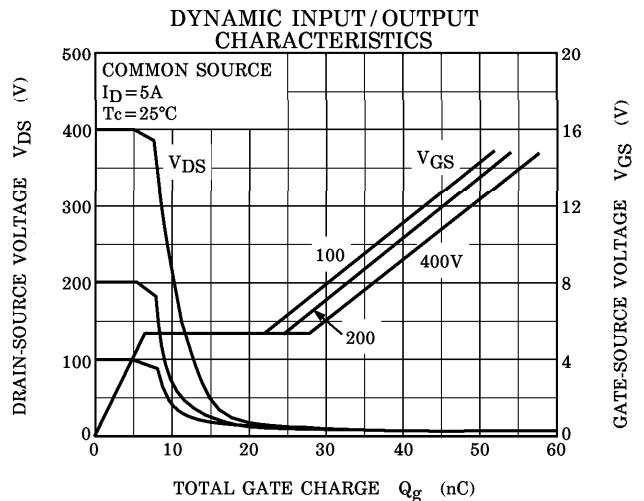
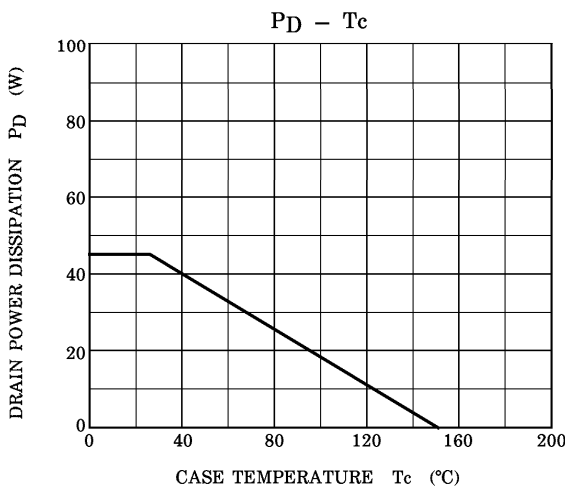
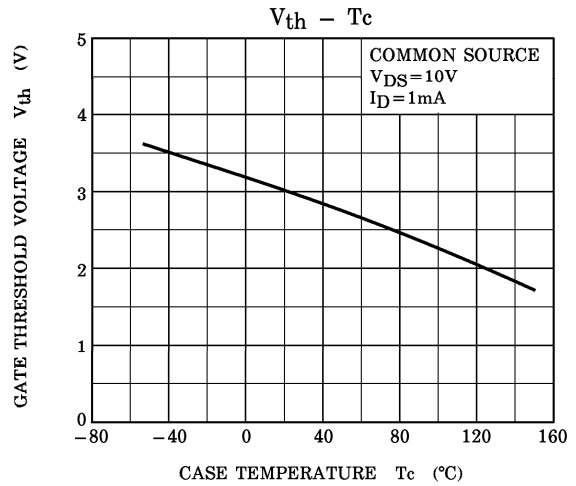
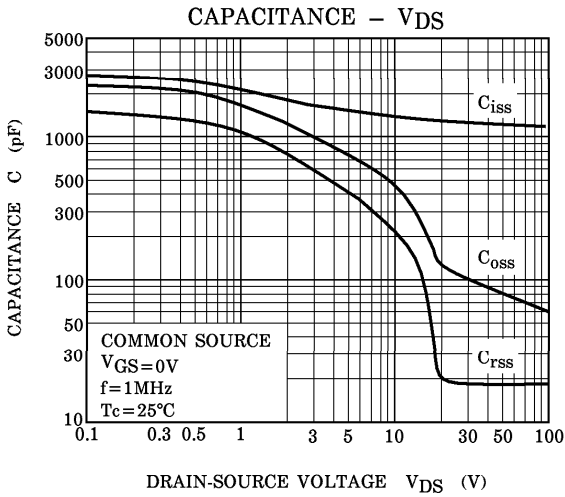
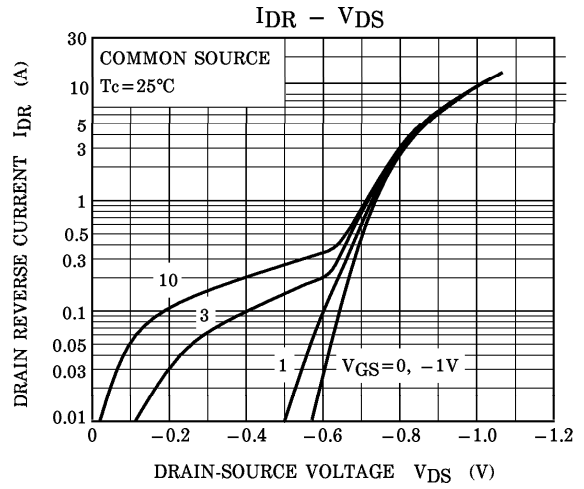
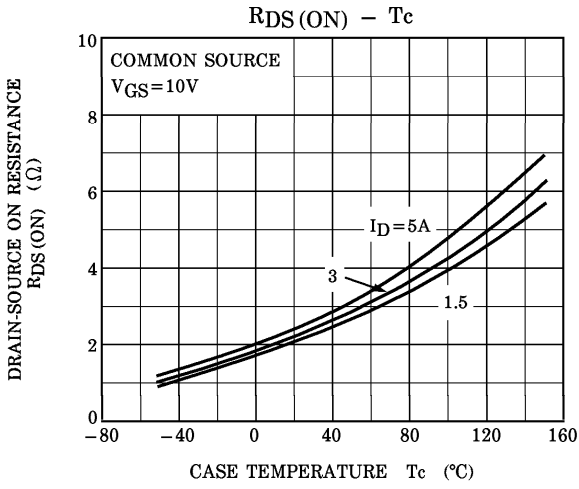
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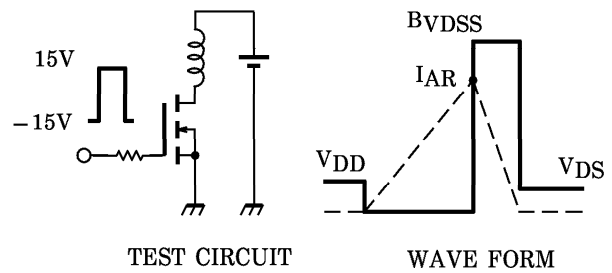
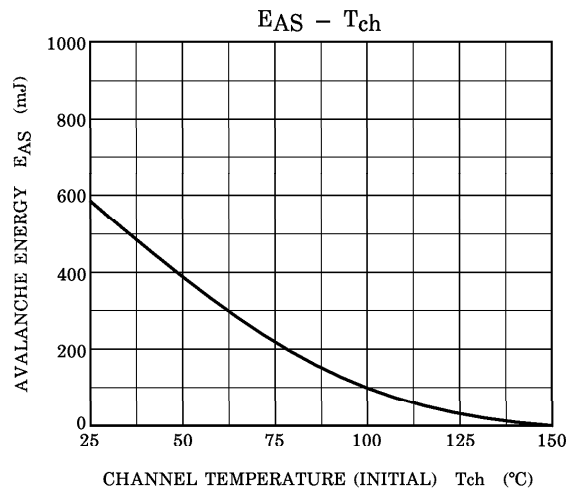
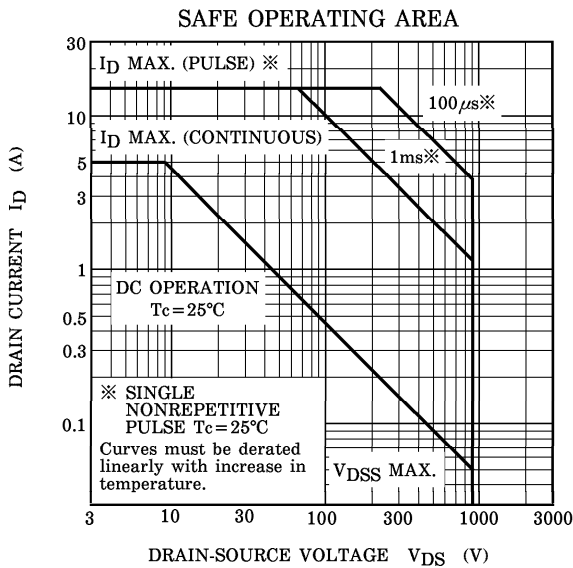
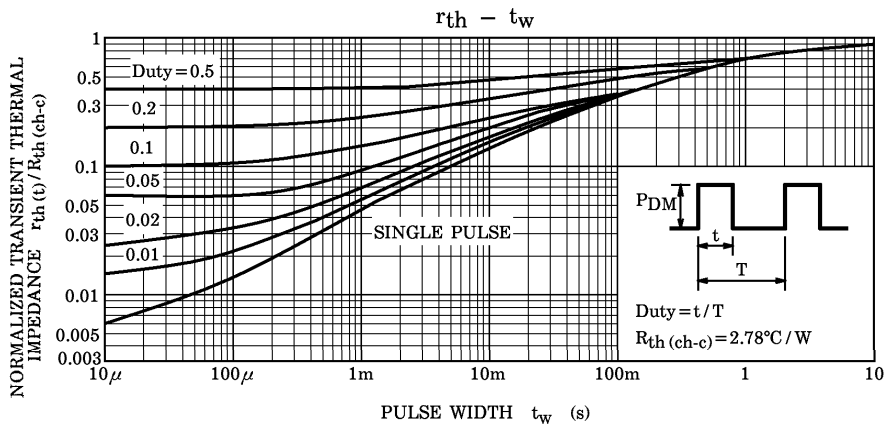


Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)







Peak $I_{AR} = 5A$, $R_G = 25\Omega$
 $V_{DD} = 90V$, $L = 43.6mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$